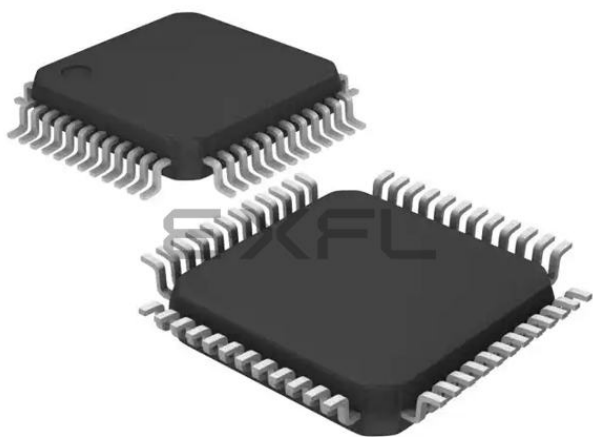




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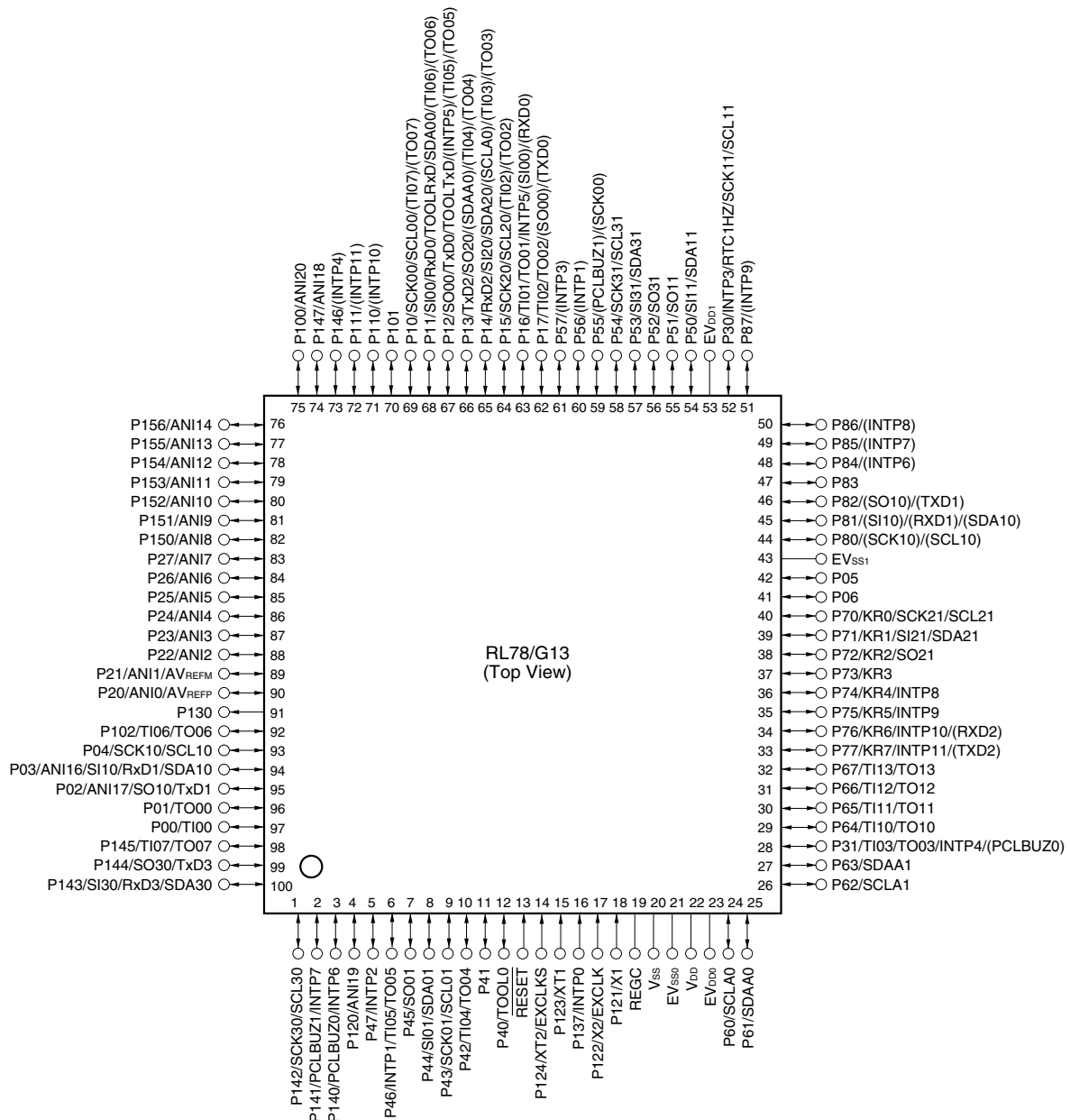
Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101gadfb-50

1.3.13 100-pin products

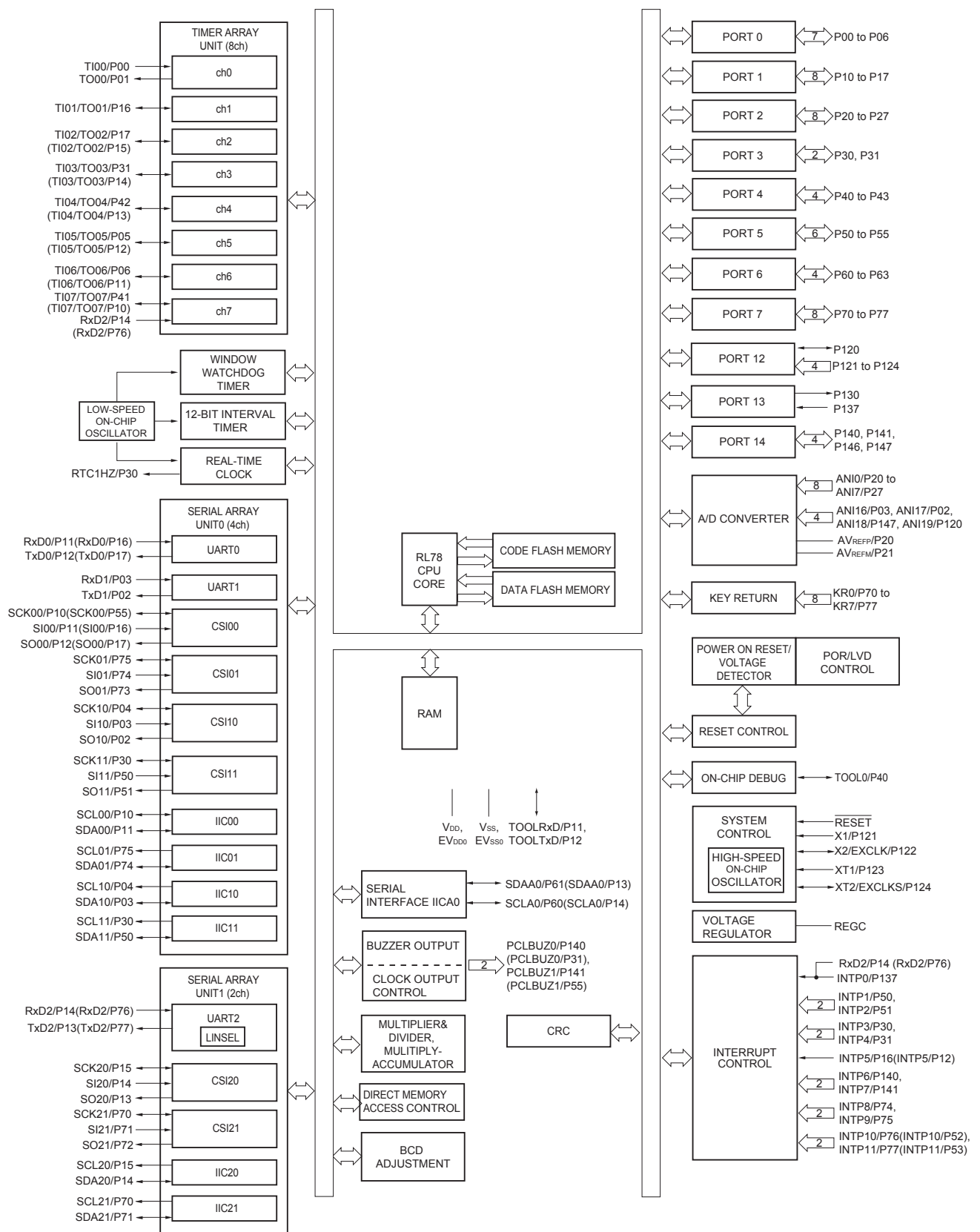
- 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



- Cautions**
1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.11 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).
3. When setting to PIOR = 1

(2/2)

Item		40-pin		44-pin		48-pin		52-pin		64-pin	
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Lx	R5F101Lx	R5F100Lx	R5F101Lx
Clock output/buzzer output		2		2		2		2		2	
		2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)									
8/10-bit resolution A/D converter		9 channels		10 channels		10 channels		12 channels		12 channels	
Serial interface		[40-pin, 44-pin products] - CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel - CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel - CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [48-pin, 52-pin products] - CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel - CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel - CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [64-pin products] - CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel - CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel - CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel									
		I ² C bus	1 channel		1 channel		1 channel		1 channel		1 channel
Multiplier and divider/multiply-accumulator		16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)									
DMA controller		2 channels									
Vectored interrupt sources	Internal	27		27		27		27		27	
	External	7		7		10		12		13	
Key interrupt		4		4		6		8		8	
Reset		- Reset by RESET pin - Internal reset by watchdog timer - Internal reset by power-on-reset - Internal reset by voltage detector - Internal reset by illegal instruction execution ^{Note} - Internal reset by RAM parity error - Internal reset by illegal-memory access									
Power-on-reset circuit		- Power-on-reset: 1.51 V (TYP.) - Power-down-reset: 1.50 V (TYP.)									
Voltage detector		- Rising edge : 1.67 V to 4.06 V (14 stages) - Falling edge : 1.63 V to 3.98 V (14 stages)									
On-chip debug function		Provided									
Power supply voltage		V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C) V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)									
Operating ambient temperature		T _A = 40 to +85°C (A: Consumer applications, D: Industrial applications) T _A = 40 to +105°C (G: Industrial applications)									

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

<R>

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EV _{SS0} , EV _{SS1}	EV _{SS0} = EV _{SS1}	-0.5 to +0.3	V
REGC pin input voltage	V _{IREGC}	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	V _{I1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	V _{I3}	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V _{O1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	V _{AI1}	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V
	V _{AI2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V

Notes 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	I _{OH1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	1.6 V ≤ EV _{DD0} ≤ 5.5 V		-10.0 ^{Note 2}	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ EV _{DD0} ≤ 5.5 V		-55.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V		-10.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V		-5.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V		-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ EV _{DD0} ≤ 5.5 V		-80.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V		-19.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V		-10.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V		-5.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ EV _{DD0} ≤ 5.5 V		-135.0 ^{Note 4}	mA
	I _{OH2}	Per pin for P20 to P27, P150 to P156	1.6 V ≤ V _{DD} ≤ 5.5 V		-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ V _{DD} ≤ 5.5 V		-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA

$$\text{Total output current of pins} = (-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = 0 V) (1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit		
Supply current ^{Note 1}	I _{DD1}	Operating mode	HS (high-speed main) mode ^{Note 5}	f _{IH} = 32 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		2.1		mA	
						V _{DD} = 3.0 V		2.1		mA	
					Normal operation	V _{DD} = 5.0 V		4.6	7.0	mA	
						V _{DD} = 3.0 V		4.6	7.0	mA	
				f _{IH} = 24 MHz ^{Note 3}	Normal operation	V _{DD} = 5.0 V		3.7	5.5	mA	
						V _{DD} = 3.0 V		3.7	5.5	mA	
				f _{IH} = 16 MHz ^{Note 3}	Normal operation	V _{DD} = 5.0 V		2.7	4.0	mA	
						V _{DD} = 3.0 V		2.7	4.0	mA	
				LS (low-speed main) mode ^{Note 5}	f _{IH} = 8 MHz ^{Note 3}	Normal operation	V _{DD} = 3.0 V		1.2	1.8	mA
							V _{DD} = 2.0 V		1.2	1.8	mA
				LV (low-voltage main) mode ^{Note 5}	f _{IH} = 4 MHz ^{Note 3}	Normal operation	V _{DD} = 3.0 V		1.2	1.7	mA
							V _{DD} = 2.0 V		1.2	1.7	mA
			HS (high-speed main) mode ^{Note 5}	f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal operation	Square wave input		3.0	4.6	mA	
						Resonator connection		3.2	4.8	mA	
					Normal operation	Square wave input		3.0	4.6	mA	
						Resonator connection		3.2	4.8	mA	
					f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 3.0 V	Normal operation	Square wave input		1.9	2.7	mA
							Resonator connection		1.9	2.7	mA
					f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal operation	Square wave input		1.9	2.7	mA
							Resonator connection		1.9	2.7	mA
				LS (low-speed main) mode ^{Note 5}	f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 3.0 V	Normal operation	Square wave input		1.1	1.7	mA
							Resonator connection		1.1	1.7	mA
					f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 2.0 V	Normal operation	Square wave input		1.1	1.7	mA
							Resonator connection		1.1	1.7	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 4} T _A = −40°C	Normal operation	Square wave input		4.1	4.9	μA	
						Resonator connection		4.2	5.0	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +25°C	Normal operation	Square wave input		4.1	4.9	μA	
						Resonator connection		4.2	5.0	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +50°C	Normal operation	Square wave input		4.2	5.5	μA	
						Resonator connection		4.3	5.6	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +70°C	Normal operation	Square wave input		4.3	6.3	μA	
						Resonator connection		4.4	6.4	μA	
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +85°C	Normal operation	Square wave input		4.6	7.7	μA	
						Resonator connection		4.7	7.8	μA	

(Notes and Remarks are listed on the next page.)

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	1.86	mA	
					V _{DD} = 3.0 V		0.62	1.86	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.45	mA	
					V _{DD} = 3.0 V		0.50	1.45	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.11	mA	
					V _{DD} = 3.0 V		0.44	1.11	mA	
				LS (low-speed main) mode Note 7	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		290	620	μA
						V _{DD} = 2.0 V		290	620	μA
				LV (low-voltage main) mode Note 7	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		440	680	μA
						V _{DD} = 2.0 V		440	680	μA
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	1.08	mA	
					Resonator connection		0.48	1.28	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.31	1.08	mA	
					Resonator connection		0.48	1.28	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.21	0.63	mA	
					Resonator connection		0.28	0.71	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.21	0.63	mA	
					Resonator connection		0.28	0.71	mA	
				LS (low-speed main) mode Note 7	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		110	360	μA
						Resonator connection		160	420	μA
			f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V		Square wave input		110	360	μA	
					Resonator connection		160	420	μA	
			Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.61	μA	
					Resonator connection		0.47	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.34	0.61	μA	
					Resonator connection		0.53	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	2.30	μA	
					Resonator connection		0.60	2.49	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.64	4.03	μA	
					Resonator connection		0.83	4.22	μA	
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.09	8.04	μA		
				Resonator connection		1.28	8.23	μA		
	I _{DD3} ^{Note 6}	STOP mode Note 8	T _A = −40°C					0.19	0.52	μA
			T _A = +25°C					0.25	0.52	μA
			T _A = +50°C					0.32	2.21	μA
			T _A = +70°C					0.55	3.94	μA
			T _A = +85°C					1.00	7.95	μA

(Notes and Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)
(1/3)(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK} 4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	300		1150		1150		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	500		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 75		t _{KCY1} /2 – 75		t _{KCY1} /2 – 75		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 170		t _{KCY1} /2 – 170		t _{KCY1} /2 – 170		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 458		t _{KCY1} /2 – 458		t _{KCY1} /2 – 458		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 12		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 18		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns

Note Use it with EV_{DD0} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI26	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V	1.2	±3.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}	1.2	±7.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875	39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57	95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625	39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±0.50	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±0.50	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±2.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±5.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±1.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V ^{Note 4}		±2.0	LSB
Analog input voltage	V _{AIN}	ANI2 to ANI14	0		AV _{REFP}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 5}			V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 5}			V

(Notes are listed on the next page.)

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V _{LVD0}	Power supply rise time	3.98	4.06	4.14	V
			Power supply fall time	3.90	3.98	4.06	V
		V _{LVD1}	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		V _{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V _{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V _{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V _{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V _{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V _{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V _{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V _{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V _{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V _{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V _{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t _{LW}		300			μs
Detection delay time						300	μs

2.8 Flash Memory Programming Characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years $T_A = 85^\circ\text{C}$	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years $T_A = 25^\circ\text{C}$		1,000,000		
		Retained for 5 years $T_A = 85^\circ\text{C}$	100,000			
		Retained for 20 years $T_A = 85^\circ\text{C}$	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_x) ^{Note}	Ceramic resonator/ crystal resonator	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1.0		20.0	MHz
		$2.4\text{ V} \leq V_{DD} < 2.7\text{ V}$	1.0		16.0	MHz
XT1 clock oscillation frequency (f_x) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

3.2.2 On-chip oscillator characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f_{IH}			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to $+85^\circ\text{C}$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-1.0		$+1.0$	%
		-40 to -20°C	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-1.5		$+1.5$	%
		$+85$ to $+105^\circ\text{C}$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-2.0		$+2.0$	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		$+15$	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

- Notes**
1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 3. When high-speed system clock and subsystem clock are stopped.
 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When $AMPHS1 = 1$ (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

3.4 AC Characteristics

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{cy}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f _{SUB}) operation		2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V			1.0		16.0	MHz
	f _{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} , t _{EXL}	2.7 V ≤ V _{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V _{DD} < 2.7 V			30			ns
	t _{EXHS} , t _{EXLS}				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	t _{TIH} , t _{TIL}				1/f _{MCK} +10			ns ^{Note}
TO00 to TO07, TO10 to TO17 output frequency	f _{TO}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV _{DD0} < 2.7 V				4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f _{PCL}	HS (high-speed main) mode	4.0 V ≤ EV _{DD0} ≤ 5.5 V				16	MHz
			2.7 V ≤ EV _{DD0} < 4.0 V				8	MHz
			2.4 V ≤ EV _{DD0} < 2.7 V				4	MHz
Interrupt input high-level width, low-level width	t _{INTH} , t _{INTL}	INTP0	2.4 V ≤ V _{DD} ≤ 5.5 V		1			μs
		INTP1 to INTP11	2.4 V ≤ EV _{DD0} ≤ 5.5 V		1			μs
Key interrupt input low-level width	t _{KR}	KR0 to KR7	2.4 V ≤ EV _{DD0} ≤ 5.5 V		250			ns
RESET low-level width	t _{RSL}				10			μs

Note The following conditions are required for low voltage interface when $\text{EV}_{\text{DD}0} < \text{V}_{\text{DD}}$
 $2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 2.7\text{ V}$: MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
 (Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).
 m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

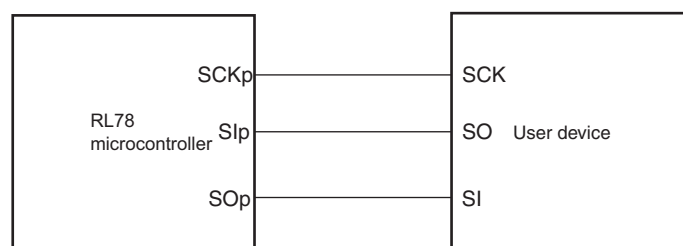
(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	t_{KCY2}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$	$20\text{ MHz} < f_{\text{MCK}}$	$16/f_{\text{MCK}}$		ns
			$f_{\text{MCK}} \leq 20\text{ MHz}$	$12/f_{\text{MCK}}$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$	$16\text{ MHz} < f_{\text{MCK}}$	$16/f_{\text{MCK}}$		ns
			$f_{\text{MCK}} \leq 16\text{ MHz}$	$12/f_{\text{MCK}}$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$16/f_{\text{MCK}}$		ns
				$12/f_{\text{MCK}}$ and 1000		ns
SCKp high-/low-level width	$t_{\text{KH2}}, t_{\text{KL2}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$t_{\text{KCY2}}/2 - 14$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$t_{\text{KCY2}}/2 - 16$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$t_{\text{KCY2}}/2 - 36$		ns
Slp setup time (to SCKp $\uparrow$) ^{Note 1}	t_{SIK2}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$1/f_{\text{MCK}} + 40$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$1/f_{\text{MCK}} + 60$		ns
Slp hold time (from SCKp $\uparrow$) ^{Note 2}	t_{KSI2}	$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$1/f_{\text{MCK}} + 62$		ns
Delay time from SCKp $\downarrow$ to SOp output ^{Note 3}	t_{KS02}	$C = 30\text{ pF}$ ^{Note 4}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$2/f_{\text{MCK}} + 66$	ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$		$2/f_{\text{MCK}} + 113$	ns

- Notes**
1. When $\text{DAPmn} = 0$ and $\text{CKPmn} = 0$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 1$. The Slp setup time becomes “to SCKp $\downarrow$ ” when $\text{DAPmn} = 0$ and $\text{CKPmn} = 1$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 0$.
 2. When $\text{DAPmn} = 0$ and $\text{CKPmn} = 0$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 1$. The Slp hold time becomes “from SCKp $\downarrow$ ” when $\text{DAPmn} = 0$ and $\text{CKPmn} = 1$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 0$.
 3. When $\text{DAPmn} = 0$ and $\text{CKPmn} = 0$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 1$. The delay time to SOp output becomes “from SCKp $\uparrow$ ” when $\text{DAPmn} = 0$ and $\text{CKPmn} = 1$, or $\text{DAPmn} = 1$ and $\text{CKPmn} = 0$.
 4. C is the load capacitance of the SOp output lines.
 5. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

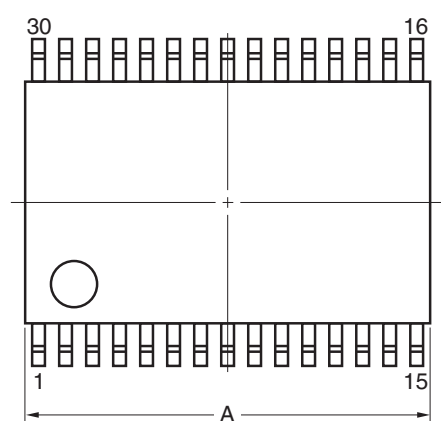
- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 2. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

CSI mode connection diagram (during communication at same potential)

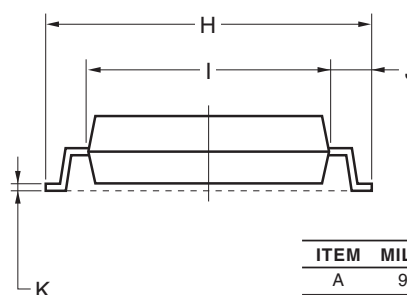
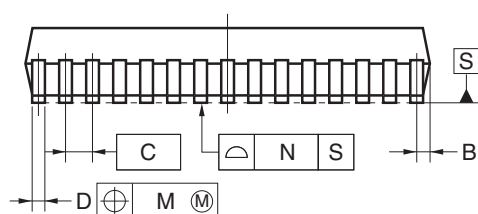
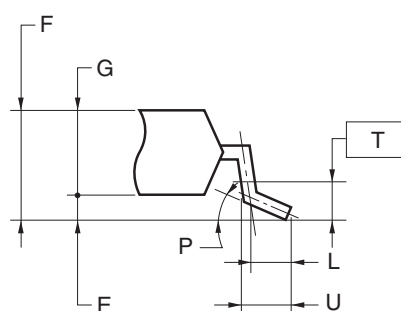
4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP
 R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP
 R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP
 R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP
 R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end

**NOTE**

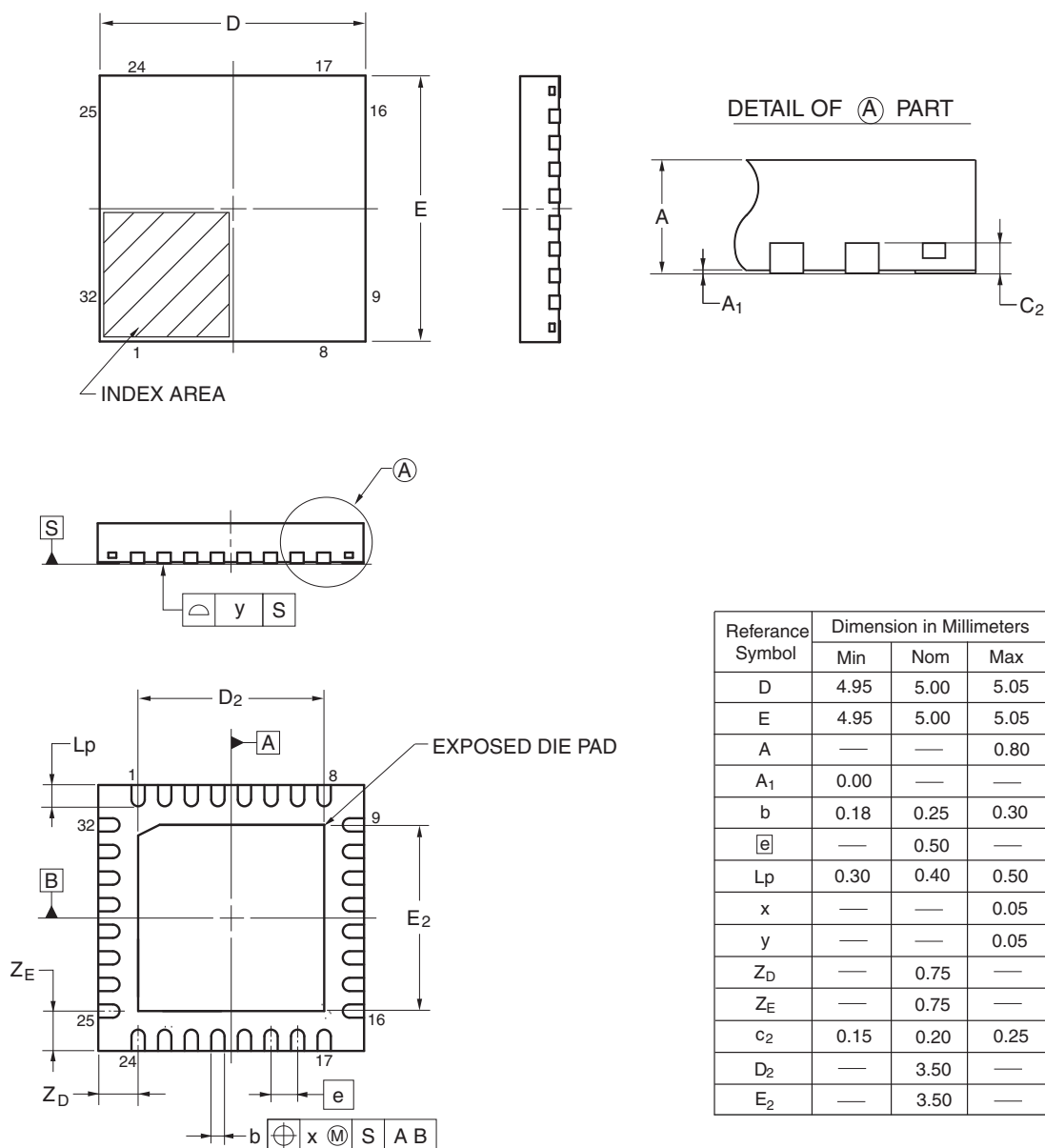
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

4.5 32-pin Products

R5F100BAANA, R5F100BCANA, R5F100BDANA, R5F100BEANA, R5F100BFANA, R5F100BGANA
 R5F101BAANA, R5F101BCANA, R5F101BDANA, R5F101BEANA, R5F101BFANA, R5F101BGANA
 R5F100BADNA, R5F100BCDNA, R5F100BDDNA, R5F100BEDNA, R5F100BFDNA, R5F100BGDNA
 R5F101BADNA, R5F101BCDNA, R5F101BDDNA, R5F101BEDNA, R5F101BFDNA, R5F101BGDNA
 R5F100BAGNA, R5F100BCGNA, R5F100BDGNA, R5F100BEGNA, R5F100BFGNA, R5F100BGGNA

JEITA Package code	RENESAS code	Previous code	MASS (TYP.)[g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-5	0.06

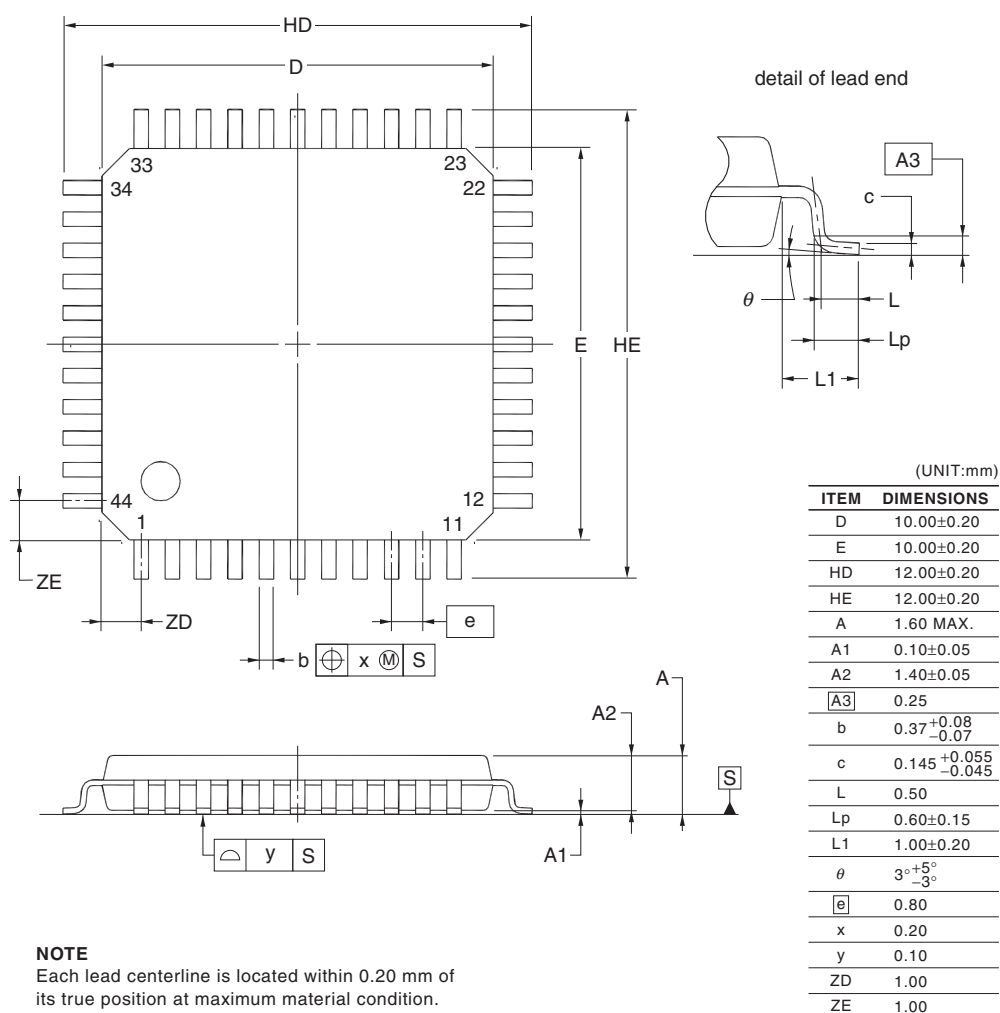


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4.8 44-pin Products

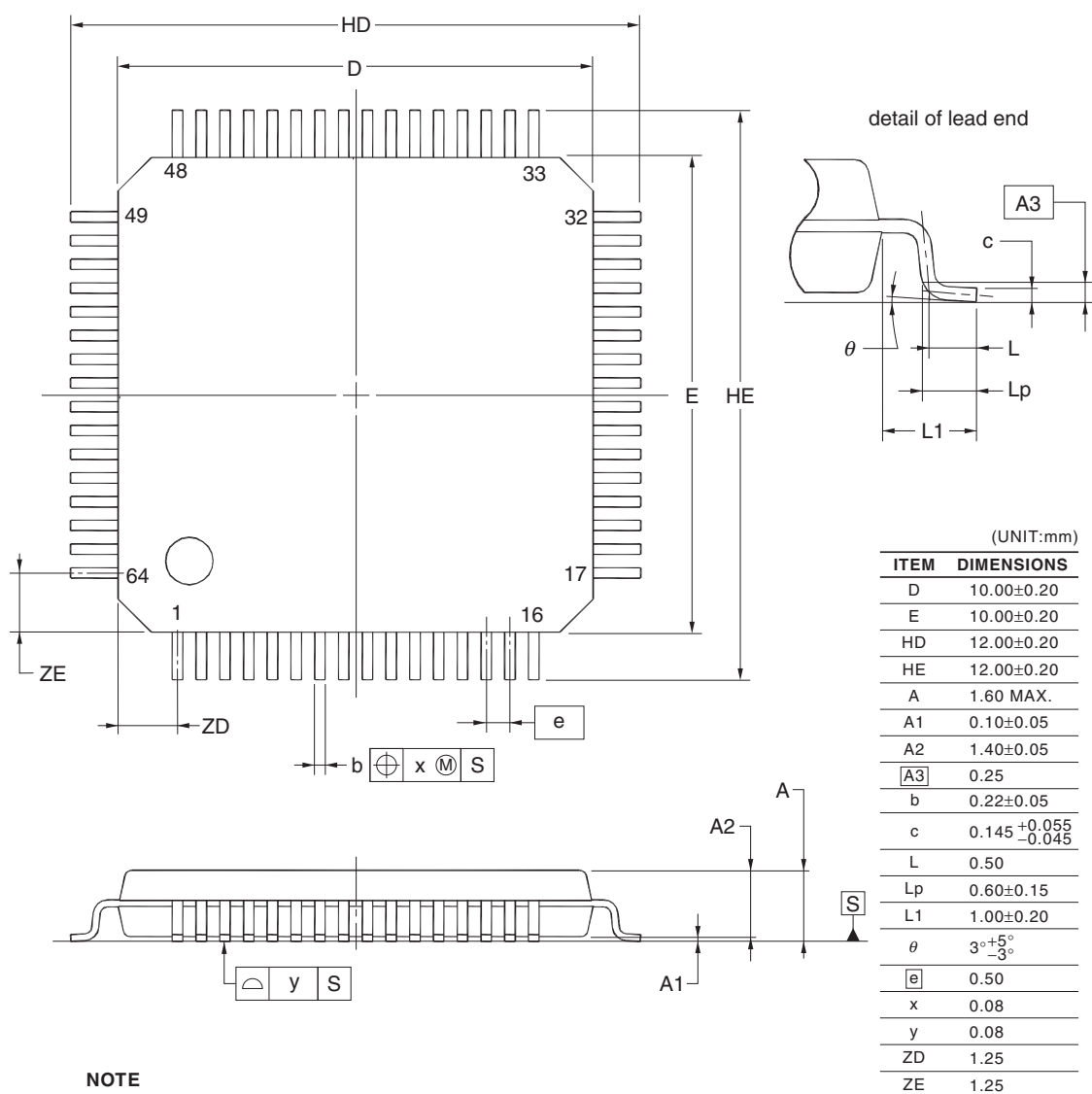
R5F100FAAFP, R5F100FCAFP, R5F100FDAFP, R5F100FEAFP, R5F100FFAFP, R5F100FGAFP,
 R5F100FHAFP, R5F100FJAFP, R5F100FKAFP, R5F100FLAFP
 R5F101FAAFP, R5F101FCAFP, R5F101FDAFP, R5F101FEAFP, R5F101FFAFP, R5F101FGAFP,
 R5F101FHAFP, R5F101FJAFP, R5F101FKAFP, R5F101FLAFP
 R5F100FADFP, R5F100FCDFP, R5F100FDDFP, R5F100FEDFP, R5F100FFDFP, R5F100FGDFP,
 R5F100FHDFP, R5F100FJDFP, R5F100FKDFP, R5F100FLDFP
 R5F101FADFP, R5F101FCDFP, R5F101FDDFP, R5F101FEDFP, R5F101FFDFP, R5F101FGDFP,
 R5F101FHDFP, R5F101FJDFP, R5F101FKDFP, R5F101FLDFP
 R5F100FAGFP, R5F100FCGFP, R5F100FDGFP, R5F100FEGFP, R5F100FFGFP, R5F100FGGFP,
 R5F100FHGFP, R5F100FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



R5F100LCAFB, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB,
 R5F100LKAFB, R5F100LLAFB
 R5F101LCAFB, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,
 R5F101LJAFB, R5F101LKAFB, R5F101LLAFB
 R5F100LCDFB, R5F100LDDFB, R5F100LEDDB, R5F100LFDDB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB,
 R5F100LKDFB, R5F100LLDFB
 R5F101LCDFB, R5F101LDDFB, R5F101LEDDB, R5F101LFDDB, R5F101LGDFB, R5F101LHDFB,
 R5F101LJDFB, R5F101LKDFB, R5F101LLDFB
 R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB,
 R5F100LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35

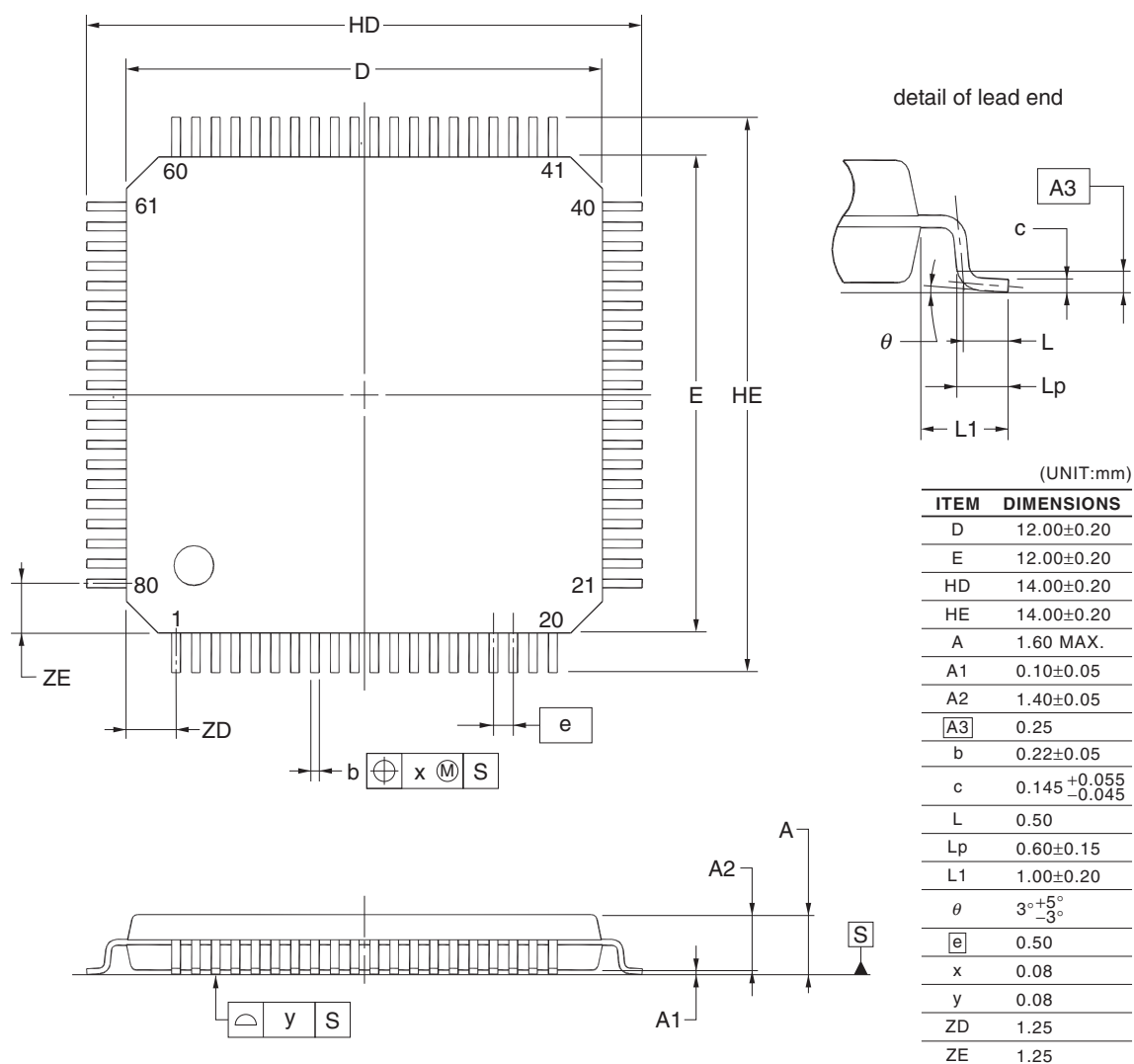


NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB
 R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB
 R5F100MFDDB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB
 R5F101MFDDB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB
 R5F100MFGFB, R5F100MGGB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53

**NOTE**

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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